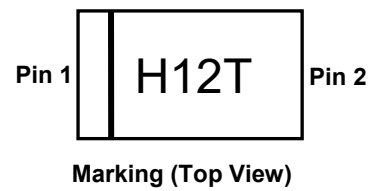
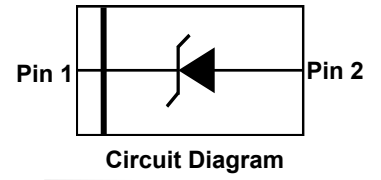


### Description

The PTVSHC2EN12VUT ESD protector is designed to replace multilayer varistors (MLVs) in portable applications such as cell phones, notebook computers, and PDA's. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, lower operating voltage, lower clamping voltage and no device degradation when compared to MLVs. The PTVSHC2EN12VUT protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events. The PTVSHC2EN12VUT is available in a DFN1610-2L package with working voltages of 12 volt. It is used to meet the ESD immunity requirements of IEC 61000-4-2, ( $\pm 30\text{kV}$  air,  $\pm 30\text{kV}$  contact discharge)



### Feature

- 3000W Peak pulse power per line ( $t_p = 8/20\mu\text{s}$ )
- DFN1610-2L package
- Response time is typically  $< 1\text{ ns}$
- Protect one I/O or power line
- Low clamping Voltage
- RoHS compliant
- Transient protection for data lines to IEC 61000-4-2(ESD)  $\pm 30\text{KV}$ (air),  $\pm 30\text{KV}$ (contact); IEC 61000-4-4 (EFT) 40A (5/50ns)

### Applications

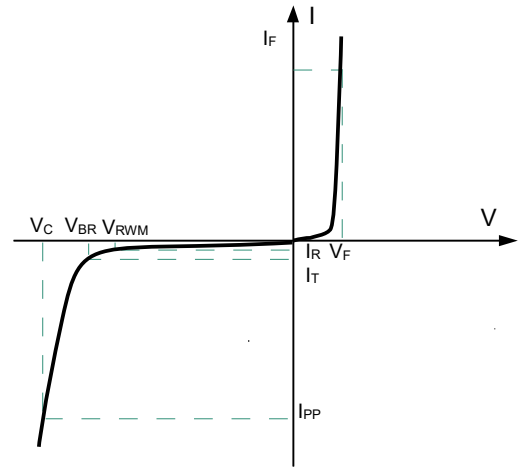
- Cell phone handsets and accessories
- Personal digital assistants (PDA's)
- Notebooks, desktops, and servers
- Portable instrumentation
- Cordless phones
- Digital cameras
- Peripherals
- MP3 players

### Mechanical Characteristics

- Lead finish: 100% matte Sn(Tin)
- Mounting position: Any
- Qualified max reflow temperature:  $260^\circ\text{C}$
- Pure tin plating:  $7 \sim 17\ \mu\text{m}$
- Pin flatness:  $\leq 3\text{mil}$
- Device meets MSL1 requirements

Electronics Parameter

Symbol	Parameter
$V_{RWM}$	Peak Reverse Working Voltage
$I_R$	Reverse Leakage Current @ $V_{RWM}$
$V_{BR}$	Breakdown Voltage @ $I_T$
$I_T$	Test Current
$I_{PP}$	Maximum Reverse Peak Pulse Current
$V_C$	Clamping Voltage @ $I_{PP}$
$P_{PP}$	Peak Pulse Power
$C_J$	Junction Capacitance
$I_F$	Forward Current
$V_F$	Forward Voltage @ $I_F$



Electrical characteristics per line@25°C ( unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Peak Reverse Working Voltage	$V_{RWM}$				12	V
Breakdown Voltage	$V_{BR}$	$I_T = 1\text{mA}$	13		16	V
Reverse Leakage Current	$I_R$	$V_{RWM} = 12\text{V}$			1	$\mu\text{A}$
Clamping Voltage	$V_C$	$I_{PP} = 50\text{A}$ $t_P = 8/20\mu\text{s}$		20	22	V
		$I_{PP} = 100\text{A}$ $t_P = 8/20\mu\text{s}$		25	27	V
Junction Capacitance	$C_J$	$V_R = 0\text{V}$ $f = 1\text{MHz}$	300	350	500	pF

Absolute maximum rating@25°C

Rating	Symbol	Value	Units
Peak Pulse Power ( $t_P = 8/20\mu\text{s}$ )	$P_{PP}$	3000	W
Lead Soldering Temperature	$T_L$	260 (10 sec)	°C
Operating Temperature	$T_J$	-55 to +125	°C
Storage Temperature	$T_{STG}$	-55 to +150	°C

Typical Characteristics

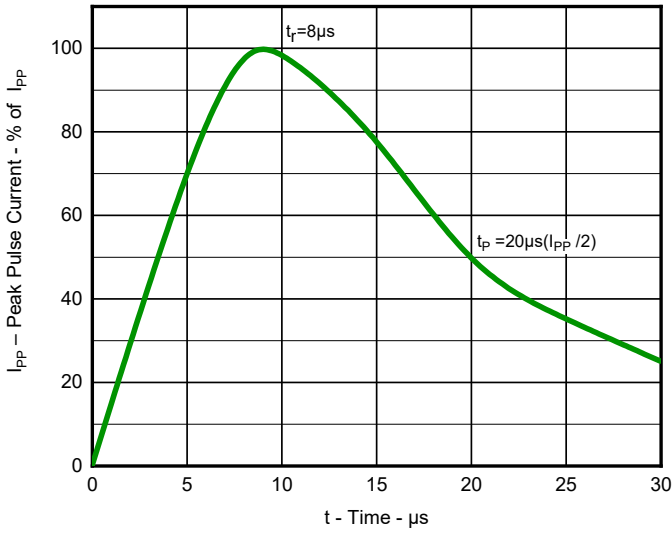


Fig 1. Pulse Waveform(8/20µs)

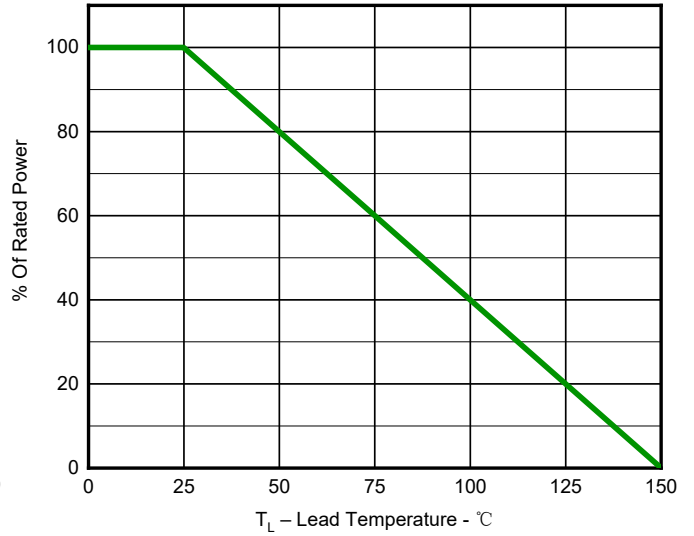


Fig 2. Power Derating Curve

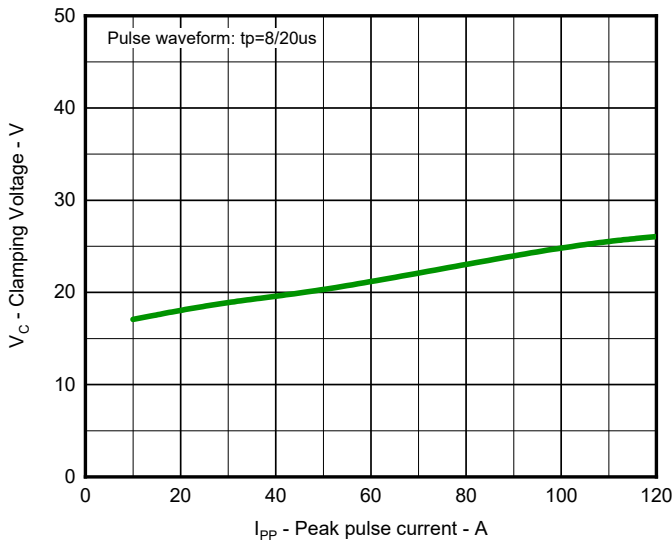


Fig 3. Clamping voltage vs. Peak pulse current

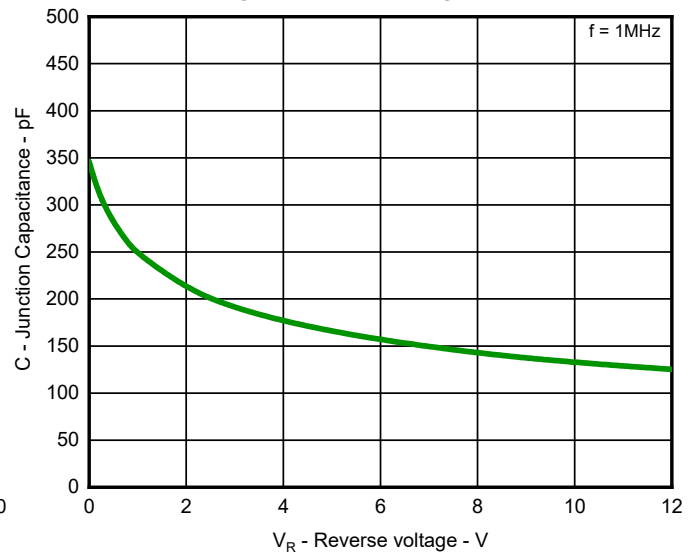


Fig 4. Capacitance vs. Reverse voltage

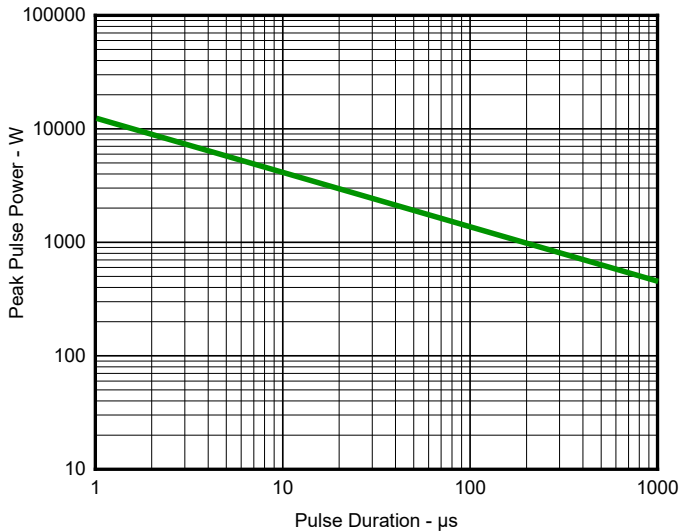


Fig 5. Non Repetitive Peak Pulse Power vs. Pulse time

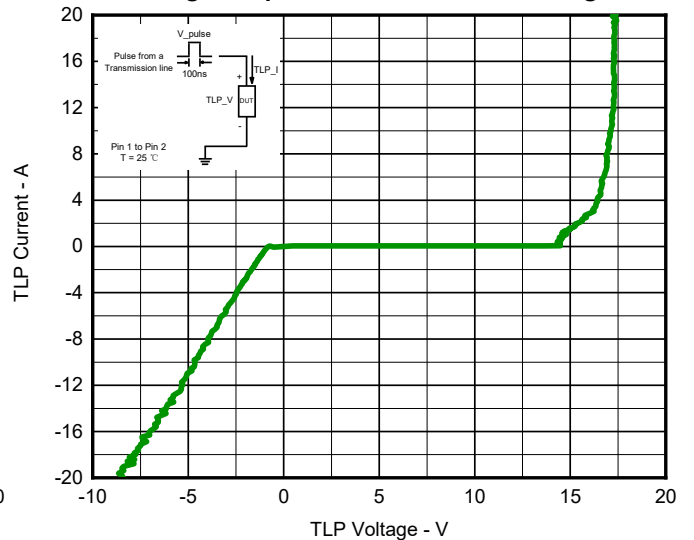
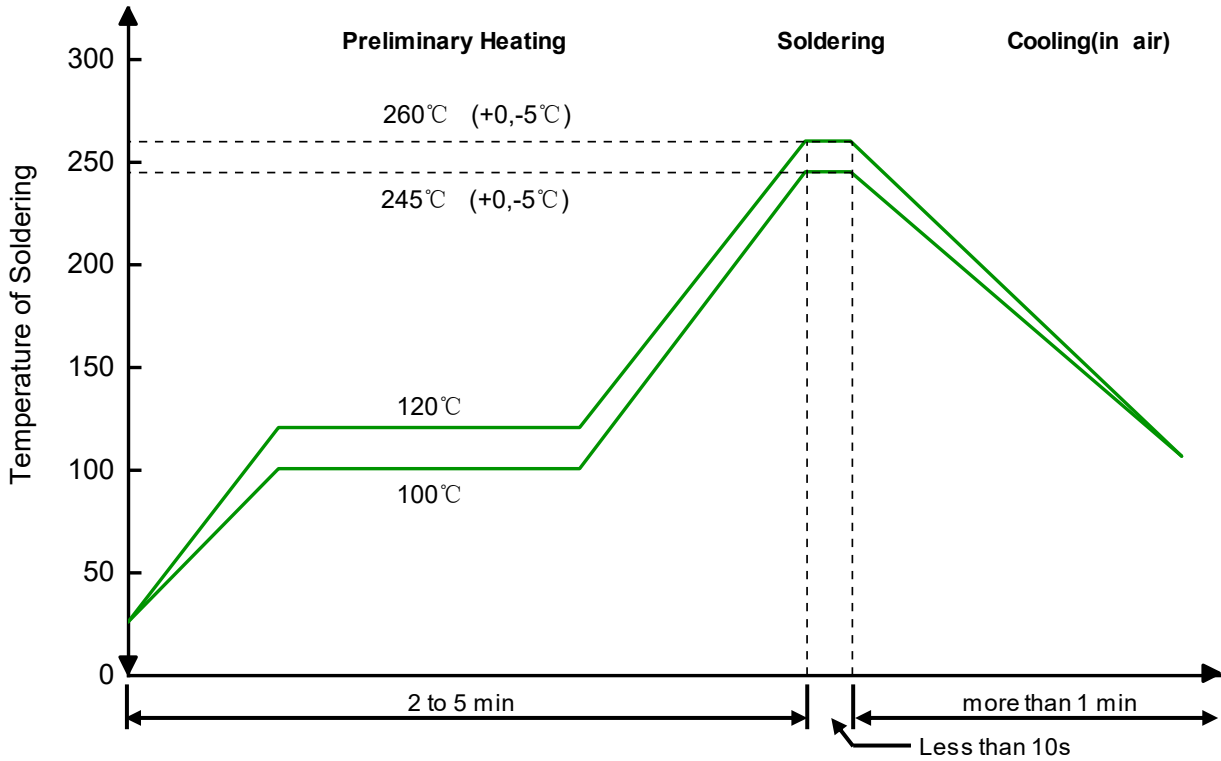


Fig 6. TLP Measurement

Solder Reflow Recommendation



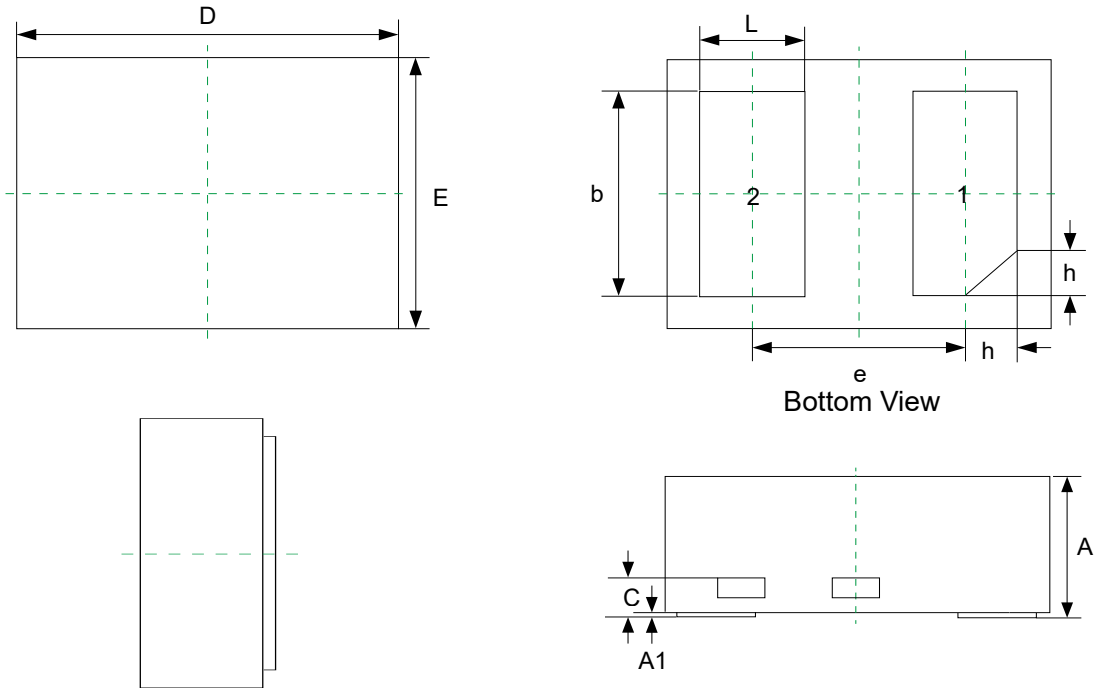
Remark: Pb free for 260°C; Pb for 245°C.

PCB Design

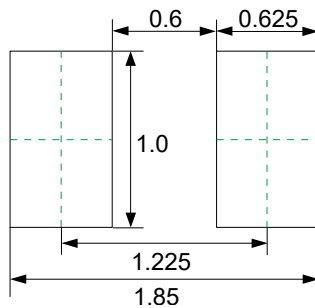
For TVS diodes a low-ohmic and low-inductive path to chassis earth is absolutely mandatory in order to achieve good ESD protection. Novices in the area of ESD protection should take following suggestions to heart:

- Do not use stubs, but place the cathode of the TVS diode directly on the signal trace.
- Do not make false economies and save copper for the ground connection.
- Place via holes to ground as close as possible to the anode of the TVS diode.
- Use as many via holes as possible for the ground connection.
- Keep the length of via holes in mind! The longer the more inductance they will have.

Product dimension (DFN1610-2L)



Dim	Millimeters	
	MIN	MAX
A	0.45	0.60
A1	--	0.05
b	0.75	0.85
c	0.10	0.20
D	1.55	1.65
e	1.10BSC	
E	0.95	1.05
L	0.35	0.45
h	0.15	0.25



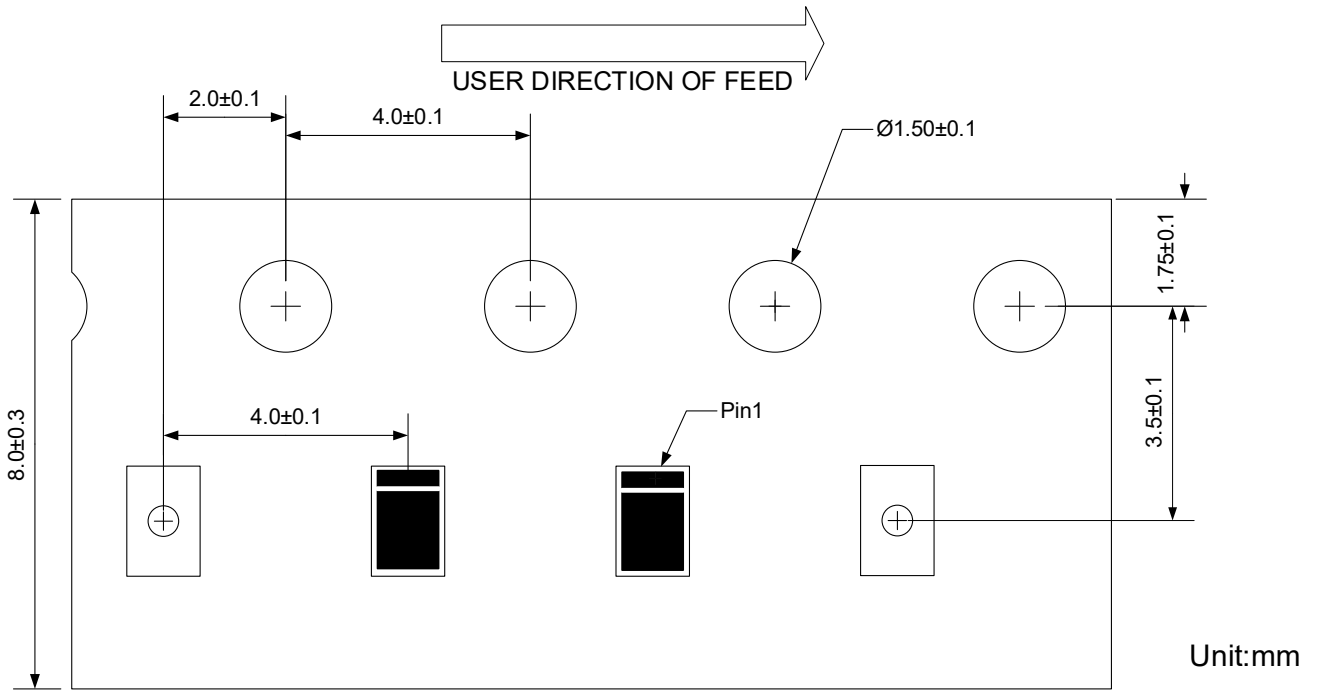
Recommended Soldering Pad

Unit:mm


Ordering information

Device	Package	Shipping
PTVSHC2EN12VUT	DFN1610-2L (Pb-Free)	3000 / Tape & Reel

Load with information




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